

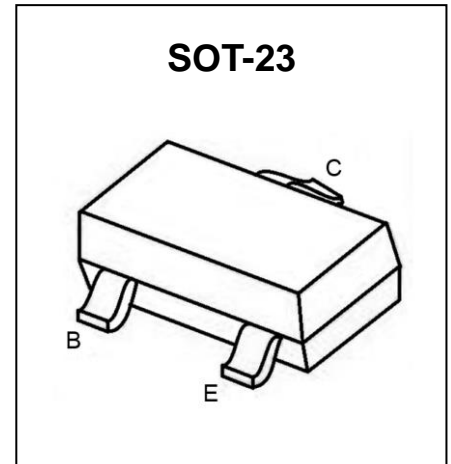


C1815 Transistor(NPN)

Feature

- Good Current Characters
- High Breakdown voltage

Marking: HF



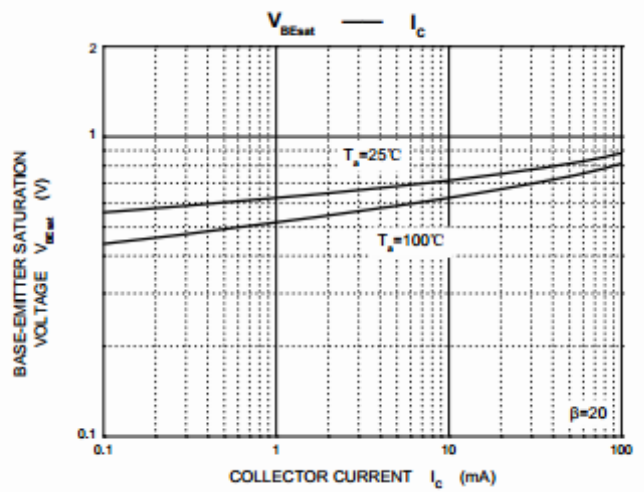
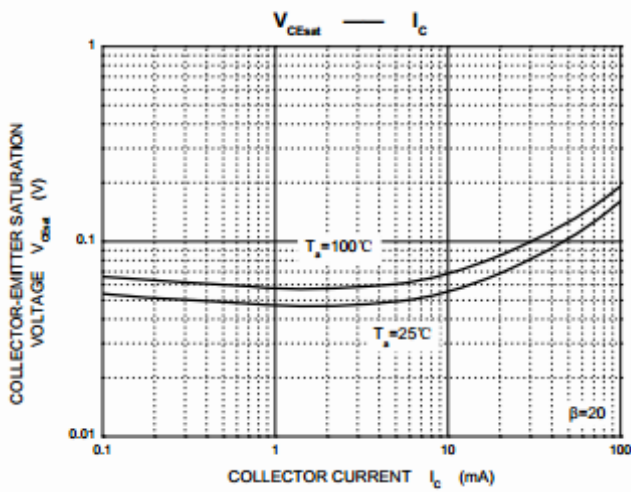
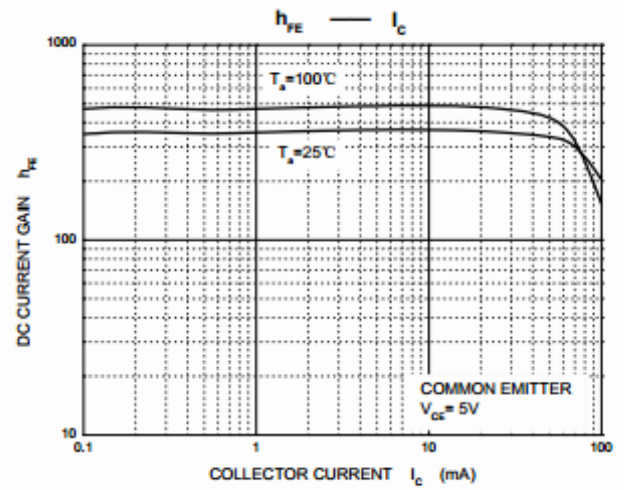
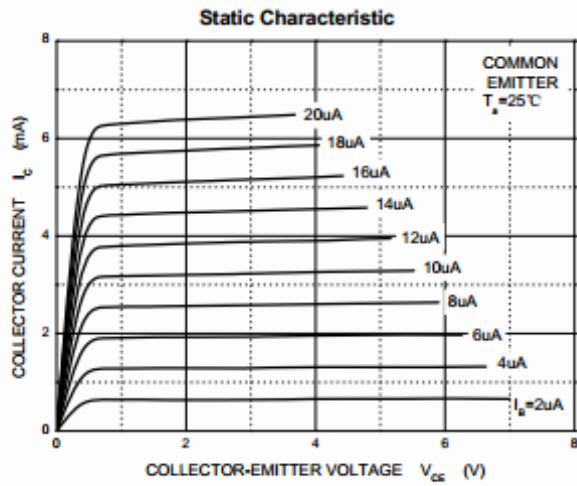
MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

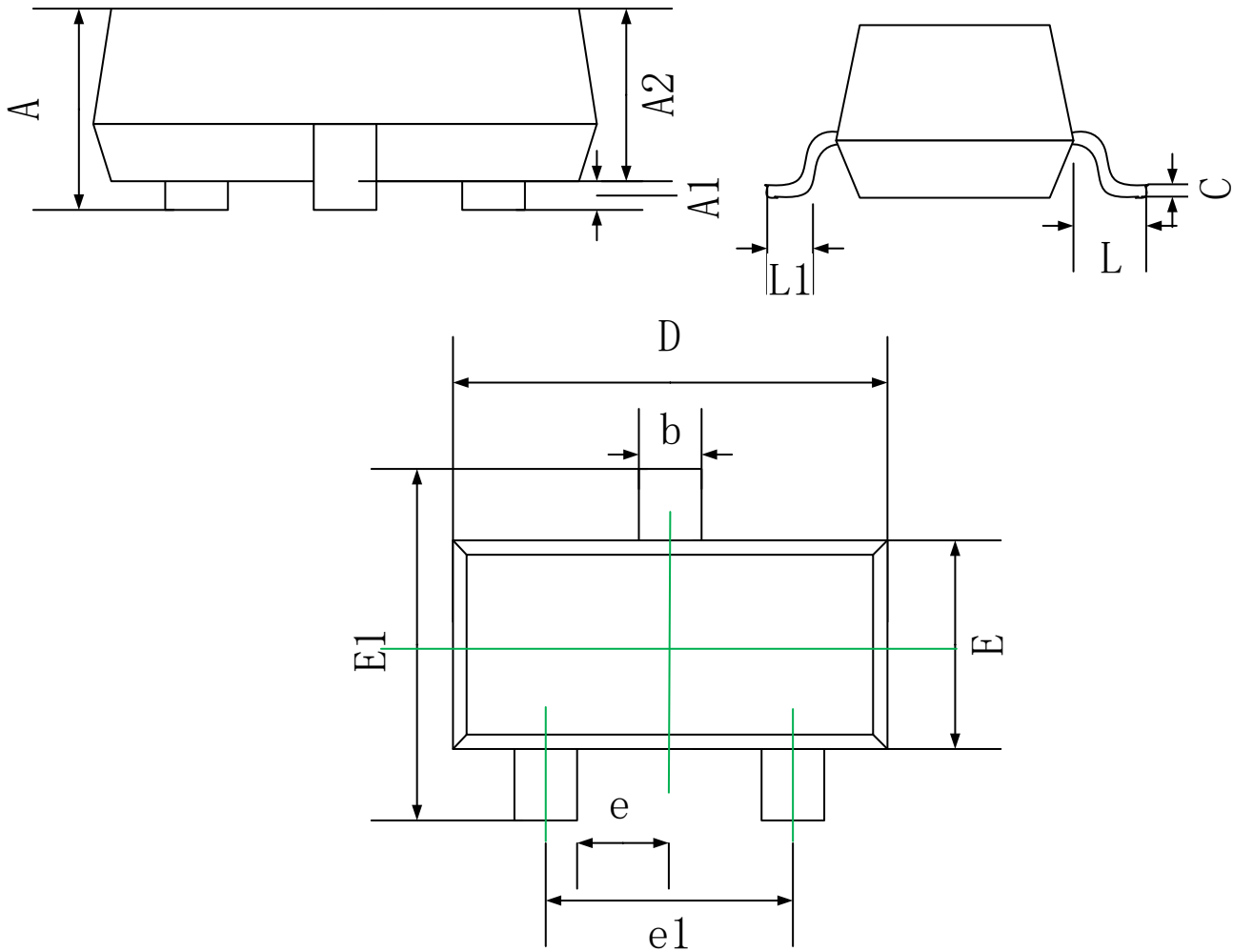
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current -Continuous	I _C	0.1	A
Power Dissipation	P _d	0.2	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	50		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	45		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5		V
Collector cut-off current	I _{CBO}	V _{CB} =40V, I _E =0		100	nA
Collector cut-off current	I _{CEO}	V _{CE} =40V, I _B =0		100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0		100	nA
DC current gain	h _{FE}	V _{CE} =5V, I _C =1mA	300	400	
Transition frequency	f _T	V _{CE} = 5V, I _C =10mA, f=30MHz	150		MHZ

Typical Characteristics



SOT-23 Package Information


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.900	1.150
A1	0.000	0.125
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950 REF.	
e1	1.800	2.000
L	0.55 REF.	
L1	0.300	0.500